OPTICAL PROXIMITY CORRECTION METHOD

Abstract

An optical proximity correction (OPC) method for modifying a photomask layout. The photomask layout includes a first photomask pattern including a first straight line and a second straight line arranged in parallel with the first straight line. The first and second straight lines have a first line-end and a second line-end respectively. The second line-end is closer to a second photomask pattern than the first line-end. The method includes performing a rule-based OPC to generate a corrected photomask layout, and adding an enhancing feature in the first line-end. The width of the enhancing feature is smaller than that of the first line. The second line-end is still closer to the second photomask pattern than the first line-end with the enhancing feature.